

09/08/2019

EE5311

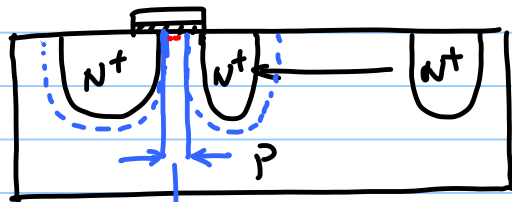
MODULE-1 - THE TRANSISTOR

SHORT CHANNEL EFFECTS

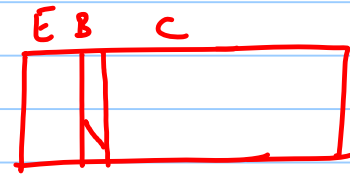
- 1) CLM
- 2) DIBL
- 3) VELOCITY SAT

LEVEL 1 SPICE MODEL : $(K', \lambda, V_{DSAT}, V_{TH0}, \gamma)$

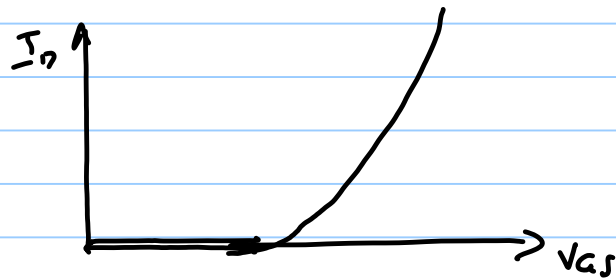
SUB THRESHOLD LEAKAGE



THIN P REGION



$$I_{\text{off}} = I_0 e^{\left(\frac{V_{GS} - V_T}{n\phi_T}\right)} (1 - e^{-V_{DS}/\phi_T}) (1 + \lambda V_{DS}) \quad (\sim \text{nA})$$



SUB THRESHOLD SLOPE (S)

$$\log_{10} I_D = \log_{10}(I_0) + \left(\frac{V_{GS} - V_T}{n \phi_T} \right) \cdot \log_{10} e + \dots$$

$$\frac{d \log_{10} I_D}{d V_{GS}} = \frac{\log_{10} e}{n \phi_T}$$

$$S = \frac{1}{\left(\frac{d \log_{10} I_D}{d V_{GS}} \right)} = \frac{n \phi_T}{\log_{10} e} = (\log_{10} e \cdot n \phi_T) \quad (1.05 = n)$$

$$= \log_{10} e \times 1.05 \times 25 \text{ mV/decade}$$

$$\sim 90 \text{ mV/decade.}$$

